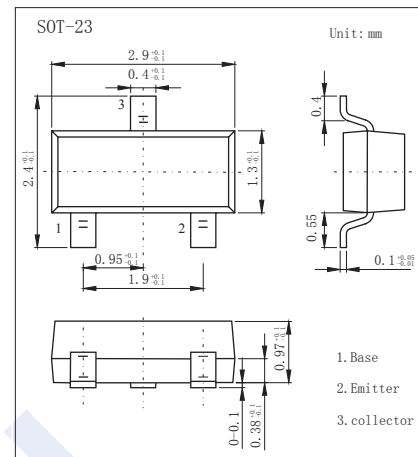


PNP Transistors

KTA1505 (KTA1505S)

■ Features

- Excellent hFE Linearity
- Complementary to KTC3876/KTC3876S



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-35	V
Collector - Emitter Voltage	V_{CE0}	-30	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_C	-500	mA
Base Current	I_B	-50	
Collector Power Dissipation $T_c = 25^\circ\text{C}$	P_C	150	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = -100 \mu\text{A}, I_E = 0$	-35			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = -1 \text{ mA}, I_B = 0$	-30			
Emitter - base breakdown voltage	V_{EB0}	$I_E = -100 \mu\text{A}, I_C = 0$	-5			
Collector-base cut-off current	I_{CB0}	$V_{CB} = -35\text{V}, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EB0}	$V_{EB} = -5\text{V}, I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$			-0.25	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$			-1.2	
Base - emitter voltage	V_{BE}	$V_{CE} = -1\text{V}, I_C = -100\text{mA}$			-1	
DC current gain	h_{FE}	$V_{CE} = -1\text{V}, I_C = -100\text{mA}$	70		400	
		$V_{CE} = -6\text{V}, I_C = -400\text{mA}$	25		40	
Collector output capacitance	C_{ob}	$V_{CB} = -6\text{V}, I_E = 0, f = 1\text{MHz}$		13		pF
Transition frequency	f_T	$V_{CE} = -6\text{V}, I_C = -20\text{mA}$		200		MHz

■ Classification of $h_{FE}(1)$

Type	KTA1505-O	KTA1505-Y	KTA1505-G
Range	70-140	120-240	200-400
Marking	AZO	AZY	AZG

PNP Transistors KTA1505 (KTA1505S)

■ Typical Characteristics

